

Zener Diode Chips (Dual Pad) for ESD Bidirectional Protection

1. Feature:

1-1 This specification applies to N/P/N silicon zener double diodes chips,
Device NO. WT-Z224V-AU4

2. Structure:

2-1. Planar type : N/P/N Diode.

2-2. Electrodes :

Top side : Gold pad.

Back side : Gold Layer.

3. Size:

3-1. Chip size : 24 mils x 24 mils (609.6 μm x 609.6 μm).

3-2. Chip thickness : 7.87 ± 1.0 mils (200 ± 2.54 μm).

3-3. Bonding pad : 19.3 mils x 19.3 mils (490 μm x 490 μm) .

3-4. Pattern drawing : Refer to the attached drawing.

* Including scribing line. The chip size is about 23mil(585 μm) after dicing.

4. Electrical Characteristics (TA=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Leakage Current	Idf	V=4V H=0mW/cm ²	-	-	100	nA
		V=5V H=0mW/cm ²	-	-	0.5	μA
	Idr	V=4V H=0mW/cm ²	-	-	100	nA
		V=5V H=0mW/cm ²	-	-	0.5	μA
Zener Voltage	Vz(forward)	Izf=5mA H=0mW/cm ²	5.5	-	7.0	V
	Vz(reverse)	Izf=5mA H=0mW/cm ²	5.3	-	6.8	
Maximum Zener Current	IzM		-	-	750	mA
Electrostatic Discharge	ESD	HBM MIL-STD883	8.0	-	-	KV

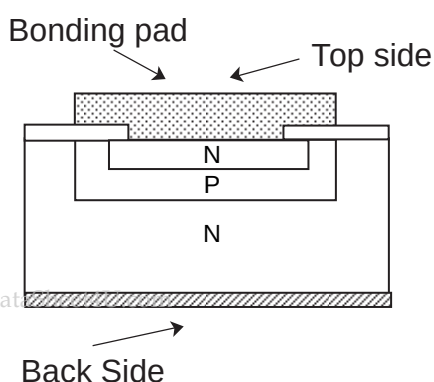
5. Annotation :

5-1. Parallel with one LED

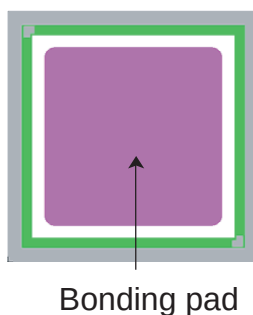
5-2. Single pad (one wire bonding applied only)

5-3. Double direction Zener diode protection

6. Drawing:



(Top View)



7. Protection Circuit:

